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List of Patents and Publications Por Applicant's Information Disclosure Statement (Use several sheets if necessary)			APPLICANT Alof Sultan e	CERTIFICATE OF FACSIMILE TRANSMISSION 37 C.F.R. § 1.6(d) i hereby certify that this correspondence is being transmitted by facsimile to the Patent and Trademark Office (Fax No. (703) 872-9308), on the date below: 5.6538 Date of transmission February 26, 2003 Signature Arman Arman Management Printed Name: Timpator M. Honeycutt					
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